

FIG. 1A

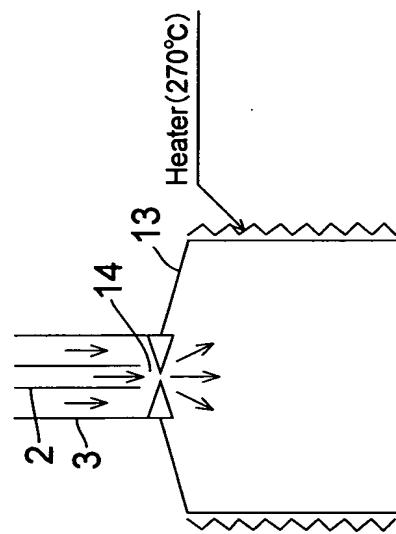


FIG. 1B

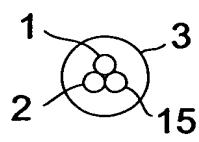


FIG.2C

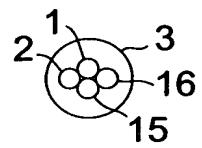
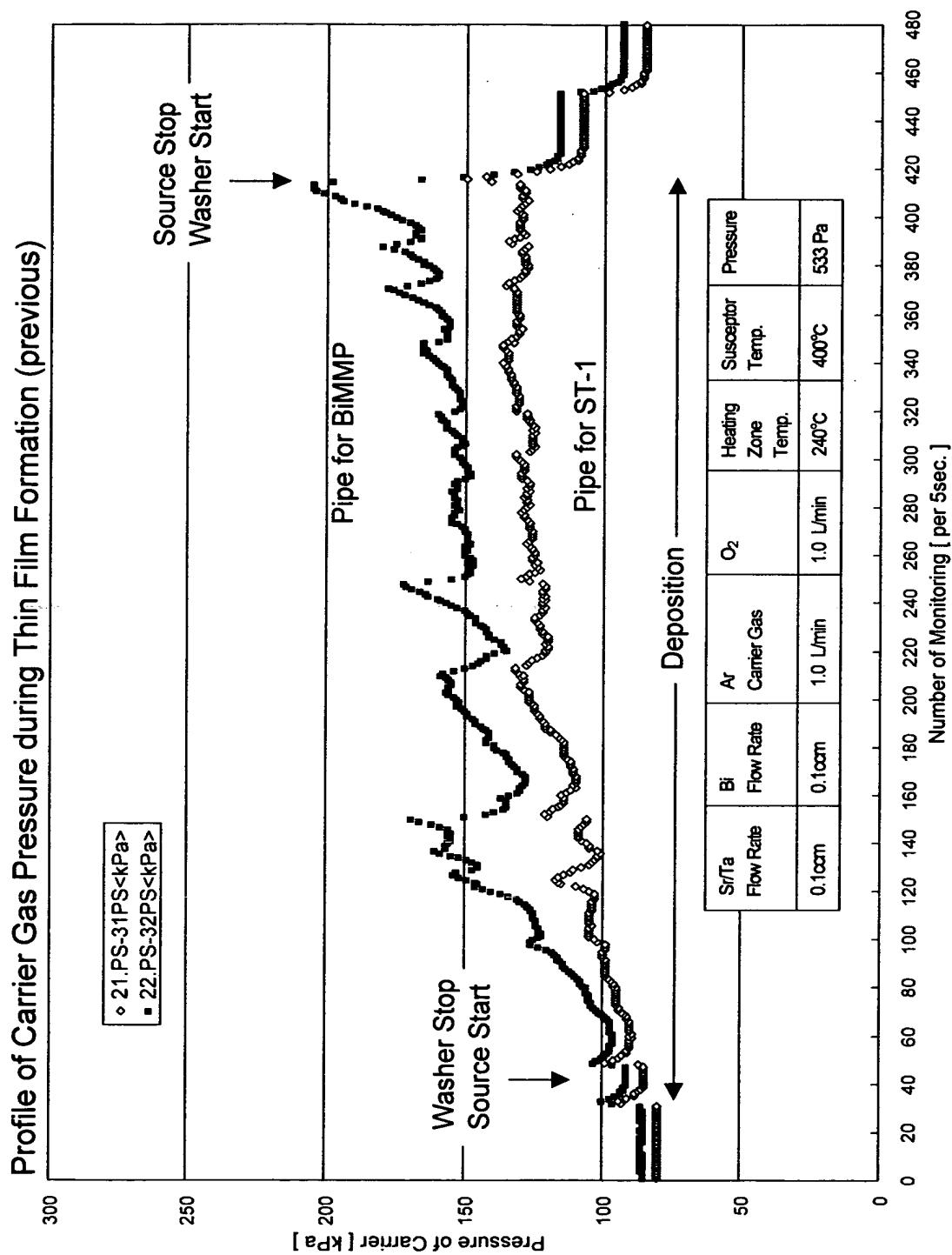
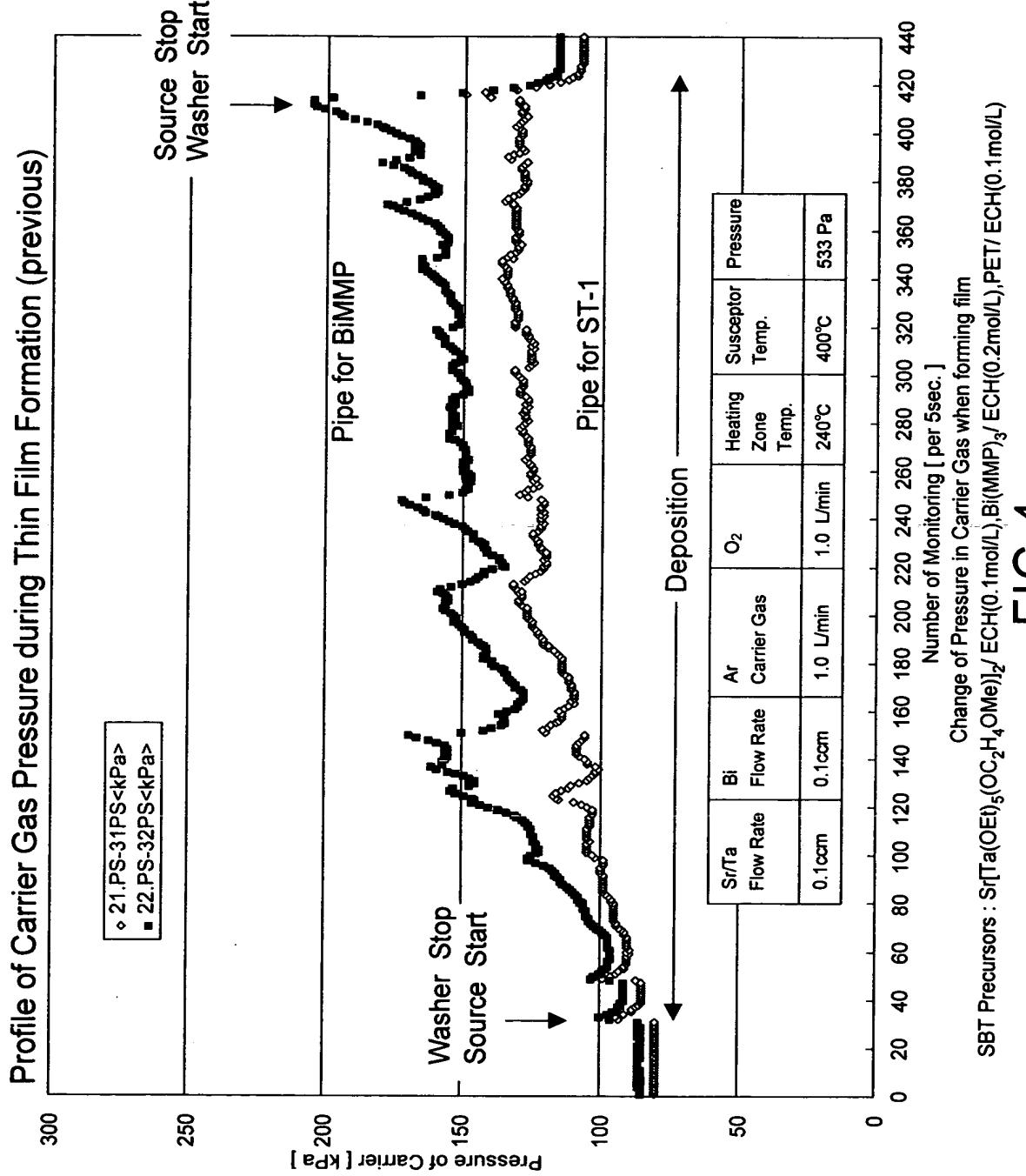
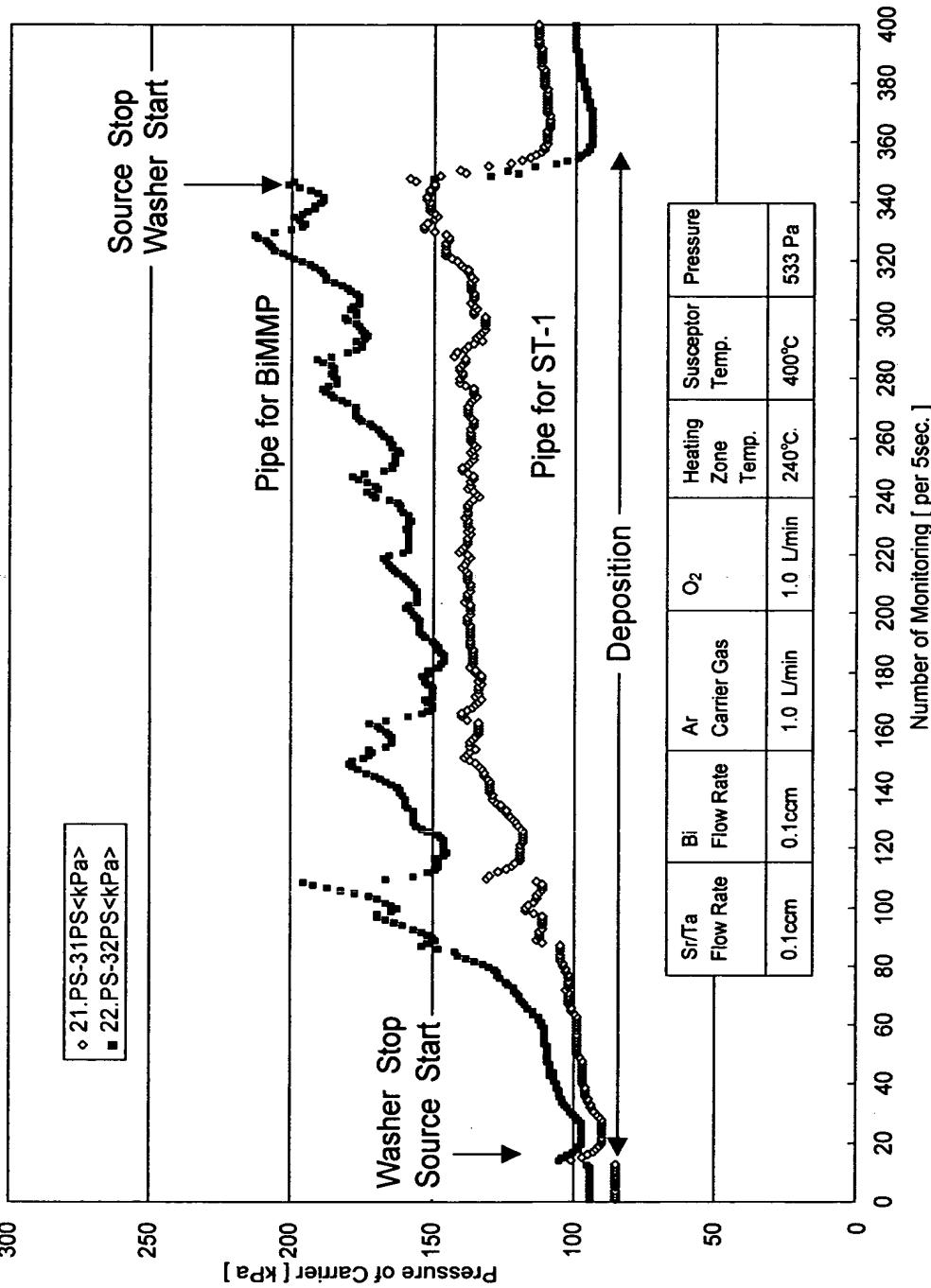


FIG.2D

**FIG. 3**

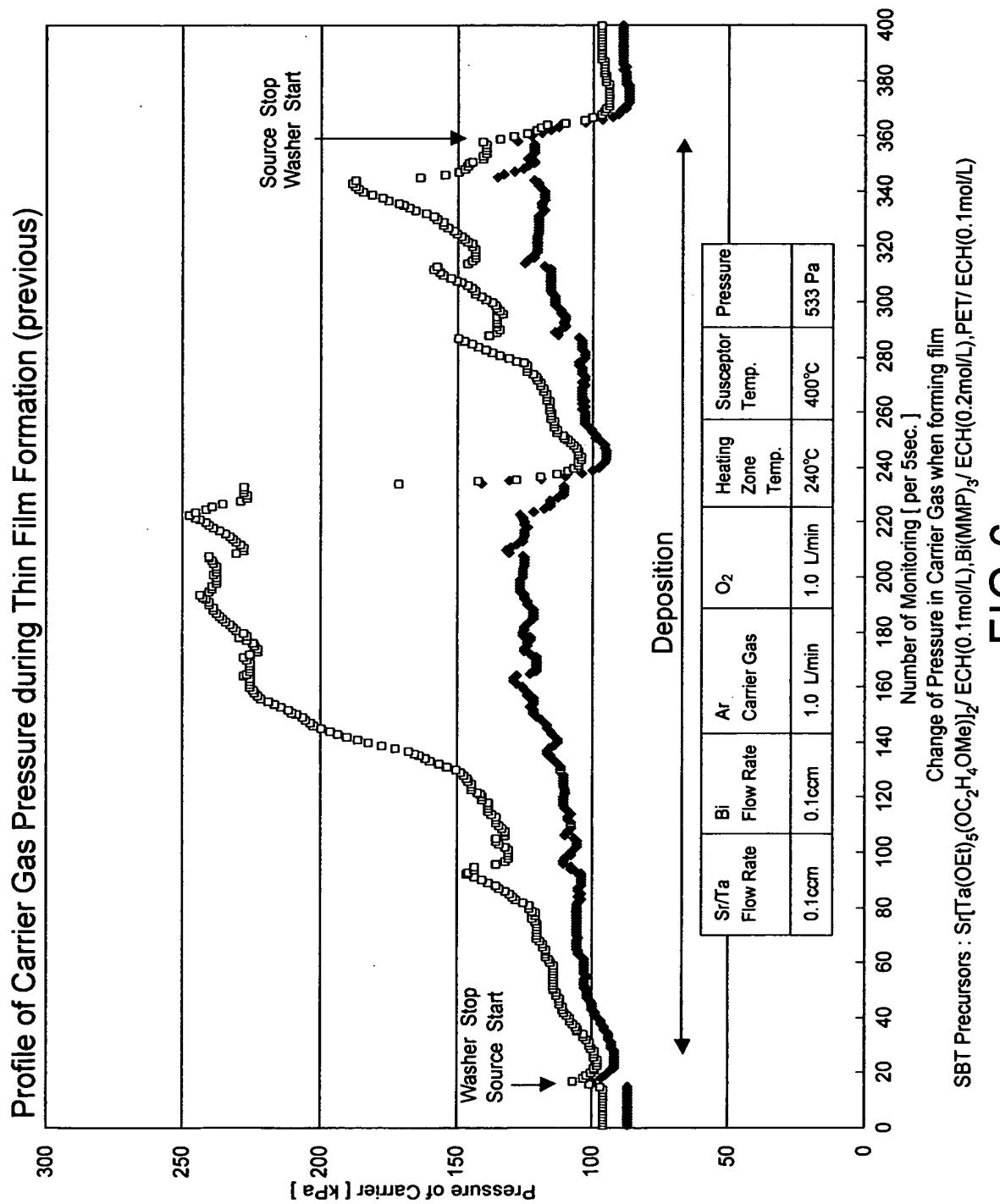


Profile of Carrier Gas Pressure during Thin Film Formation (previous)



Change of Pressure in Carrier Gas when forming film
 SBT Precursors : Sr(Ta(OEt)₅(OC₂H₄OMe))₂/ECH(0.1mol/L), Bi(MMP)₃/ECH(0.2mol/L), PET/ECH(0.1mol/L)

FIG. 5

**FIG. 6**

Profile of Carrier Gas Pressure during Thin Film Formation (previous)

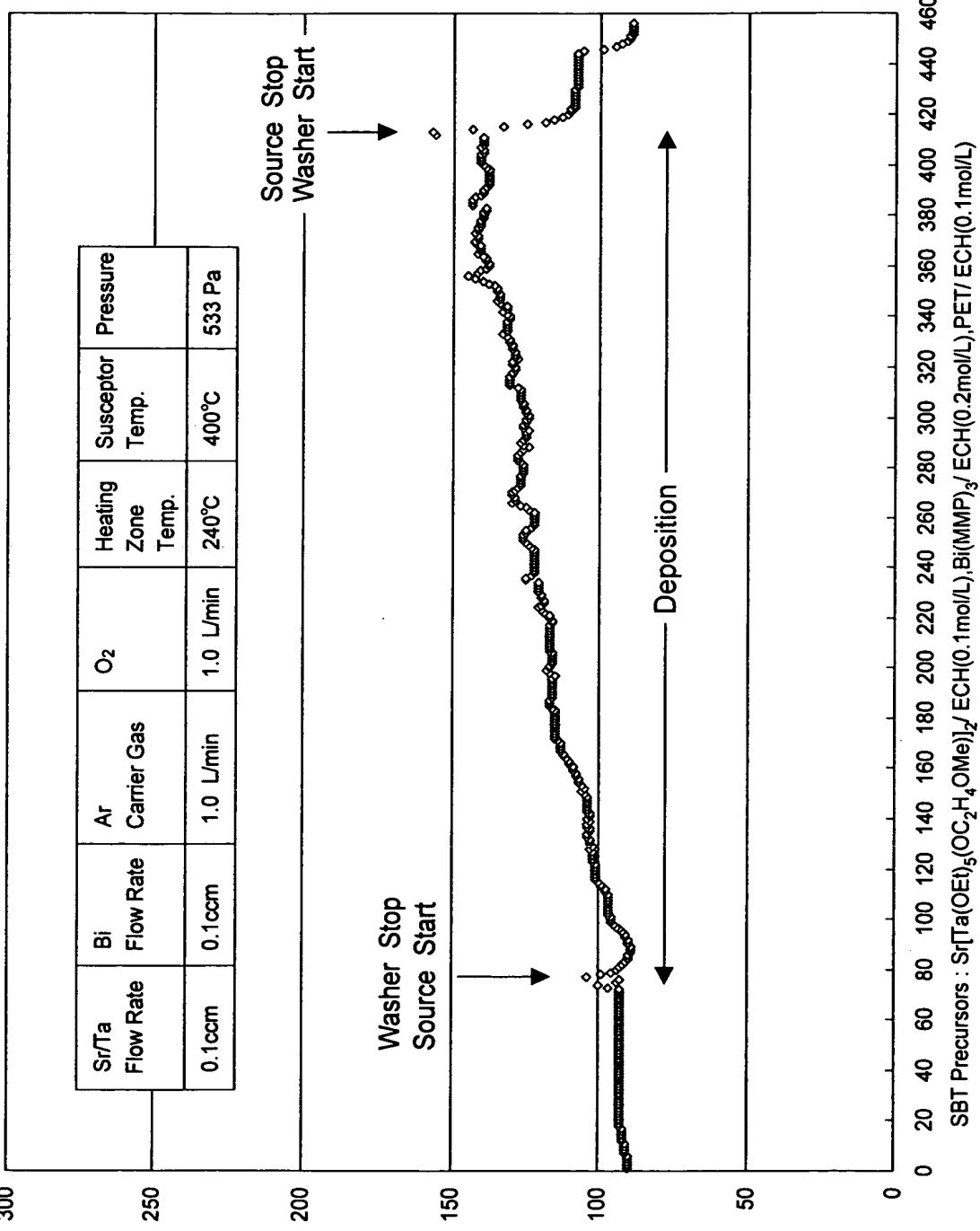
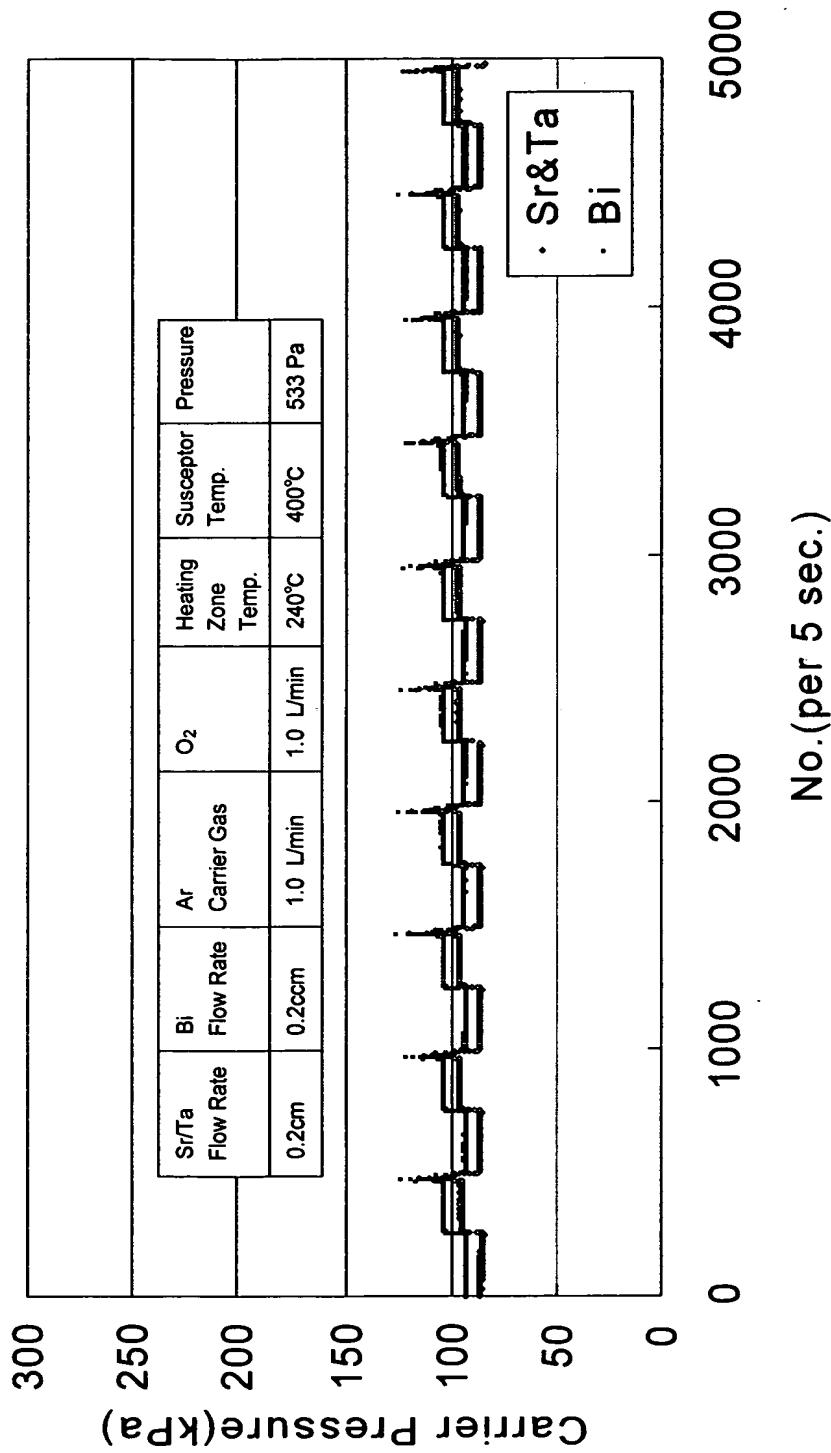


FIG. 7

Profile of Carrier Gas Pressure during Thin Film Formation (Current)



SBT Precursors : Sr[Ta(OEt)₅(OC₂H₄OMe)]₂/ ECH(0.05mol/L), Bi(MMP)₃/ ECH(0.1mol/L), PET/ ECH(0.05mol/L)

FIG. 8

Continuous Running Test Result (SBT Depo. Rate, Si Wafer)

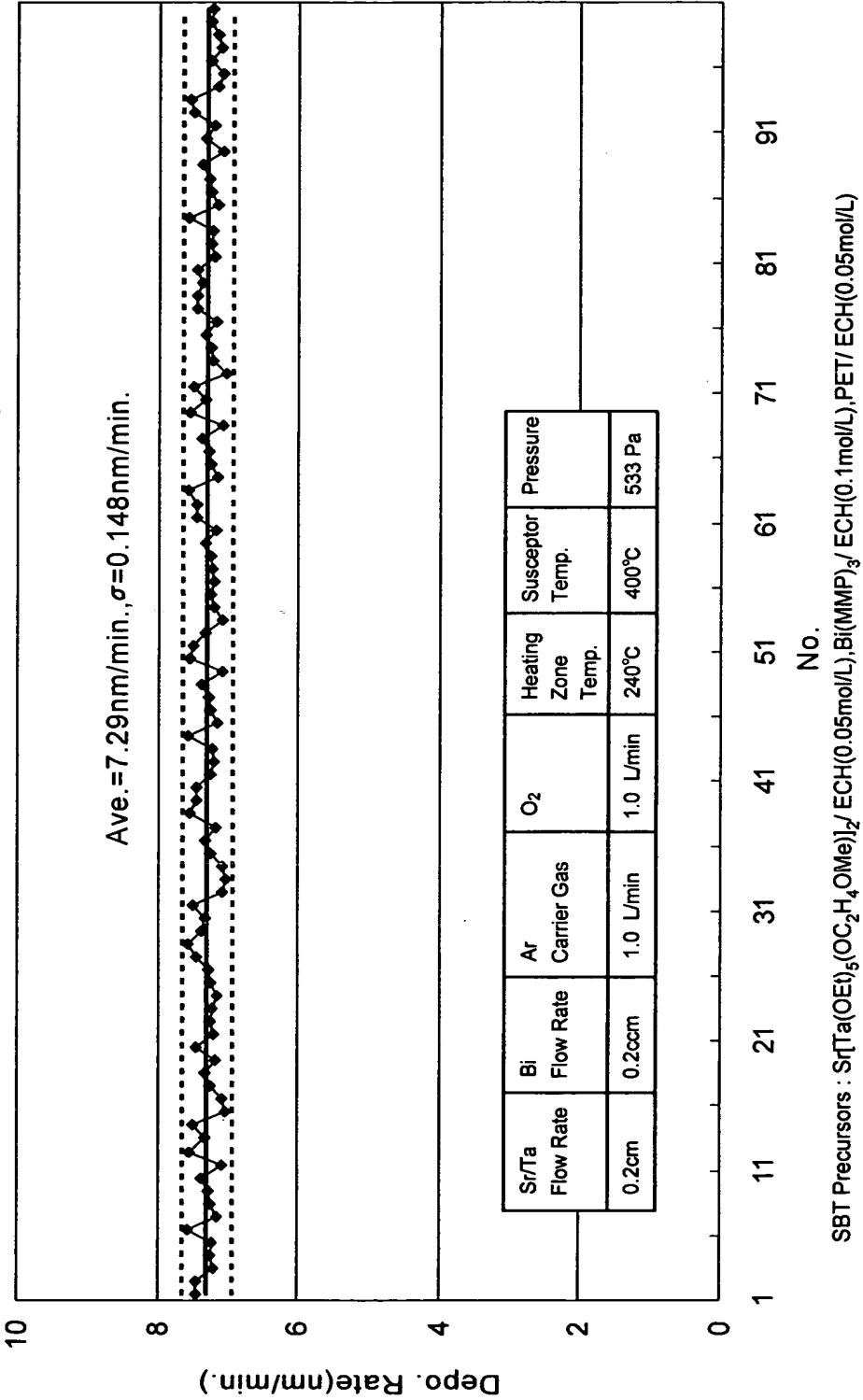


FIG.9

Continuous Running Test Result (SBT Composition, Si Wafer)

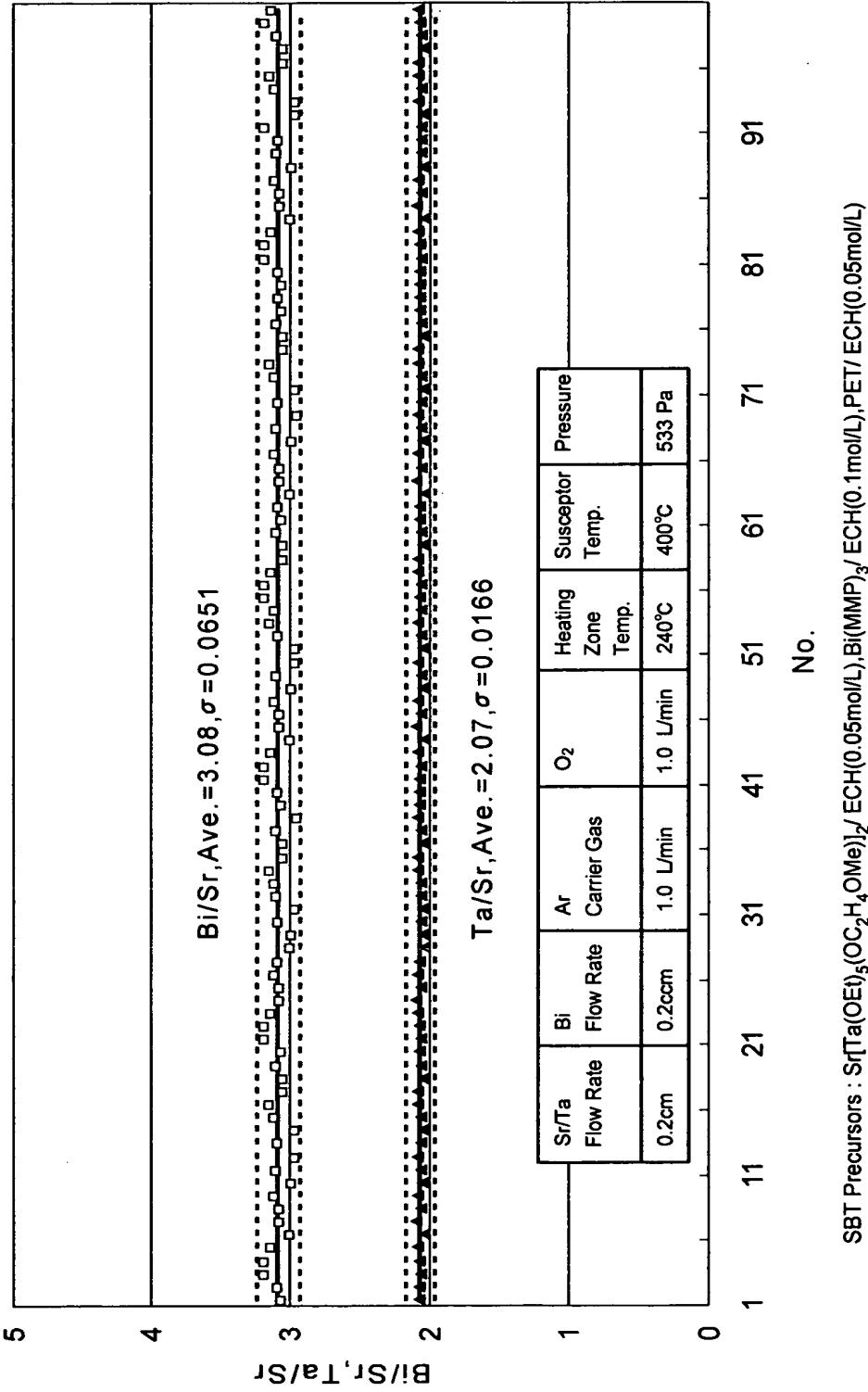


FIG.10

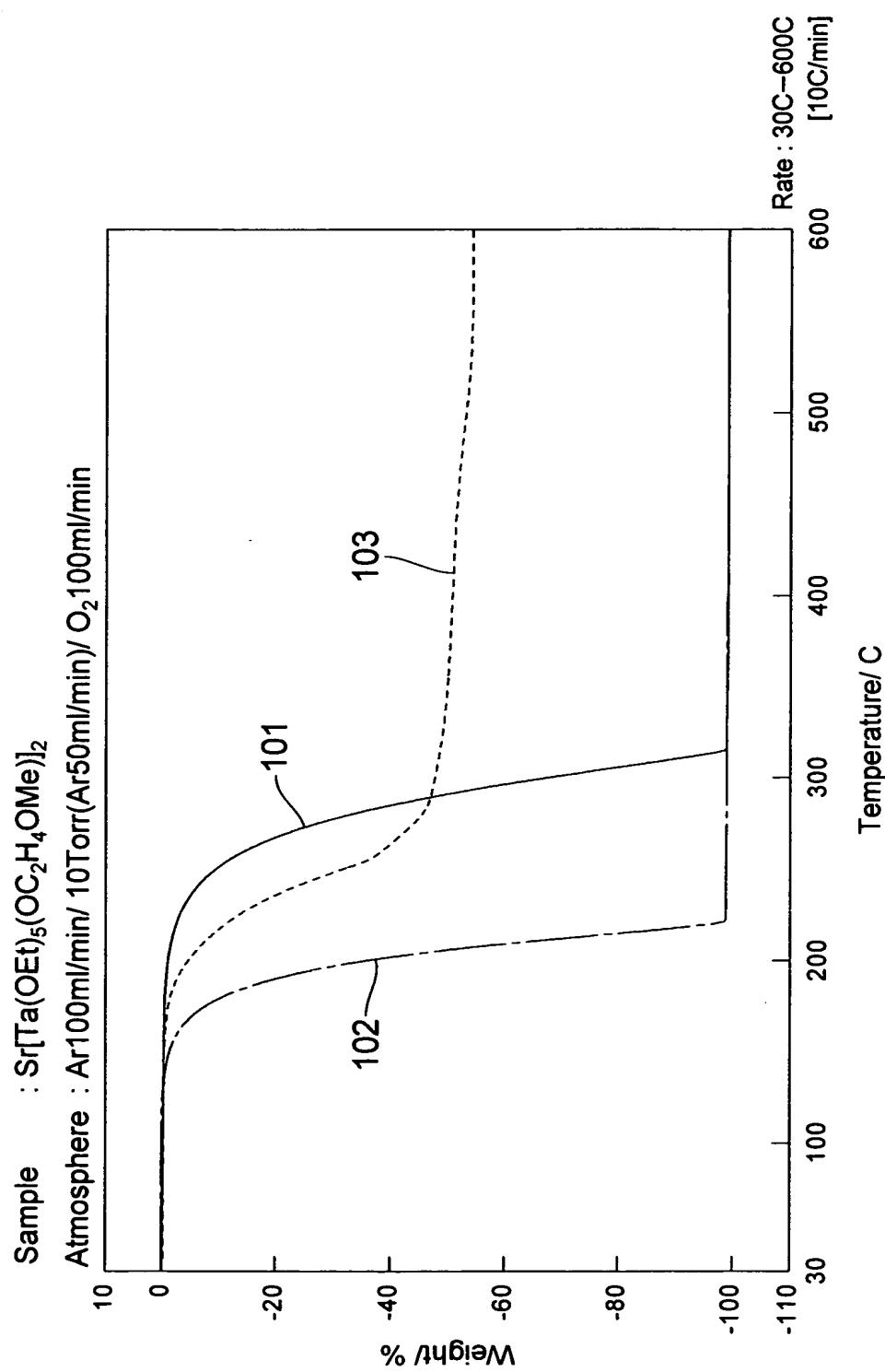


FIG.11

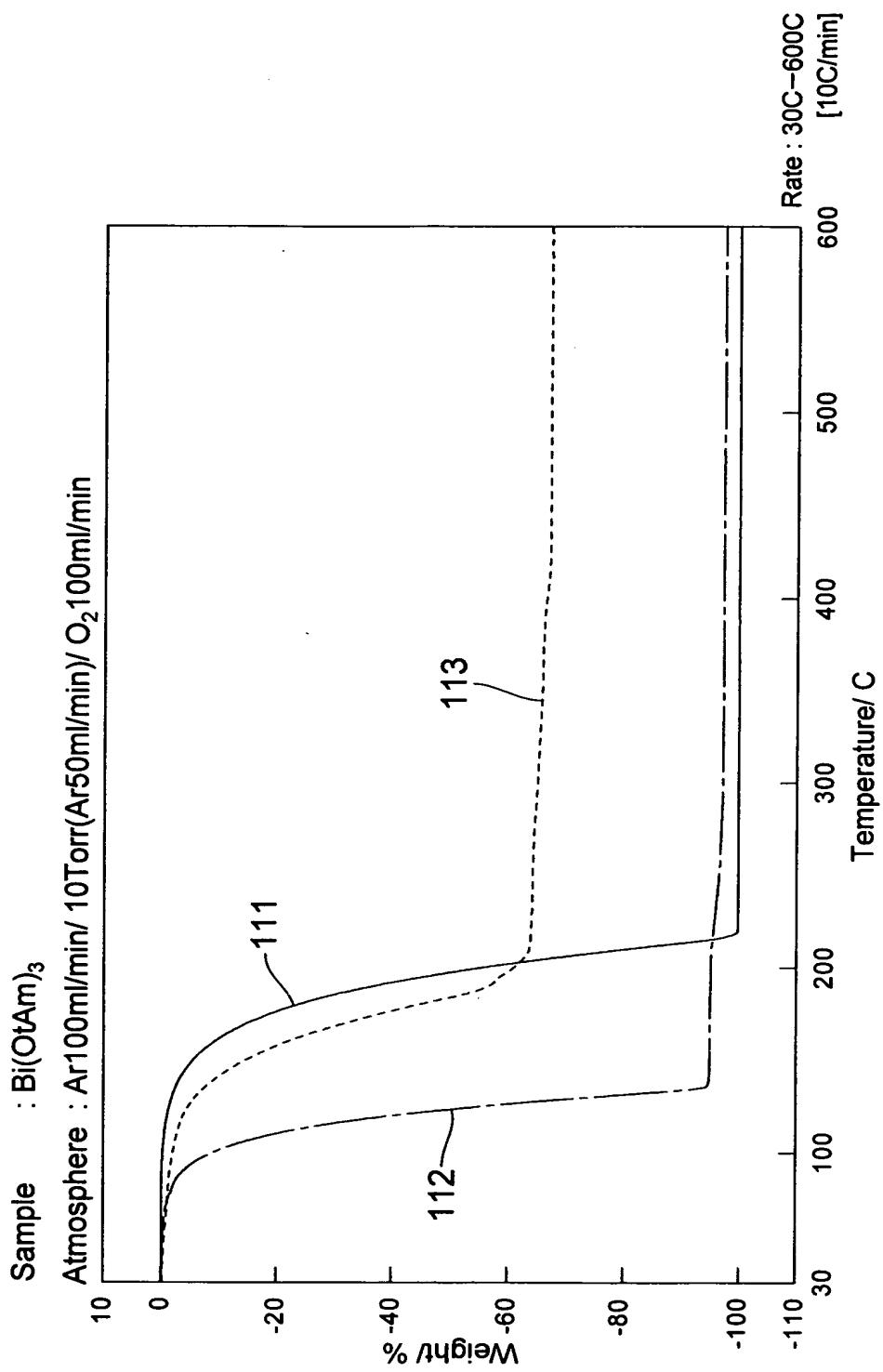


FIG.12

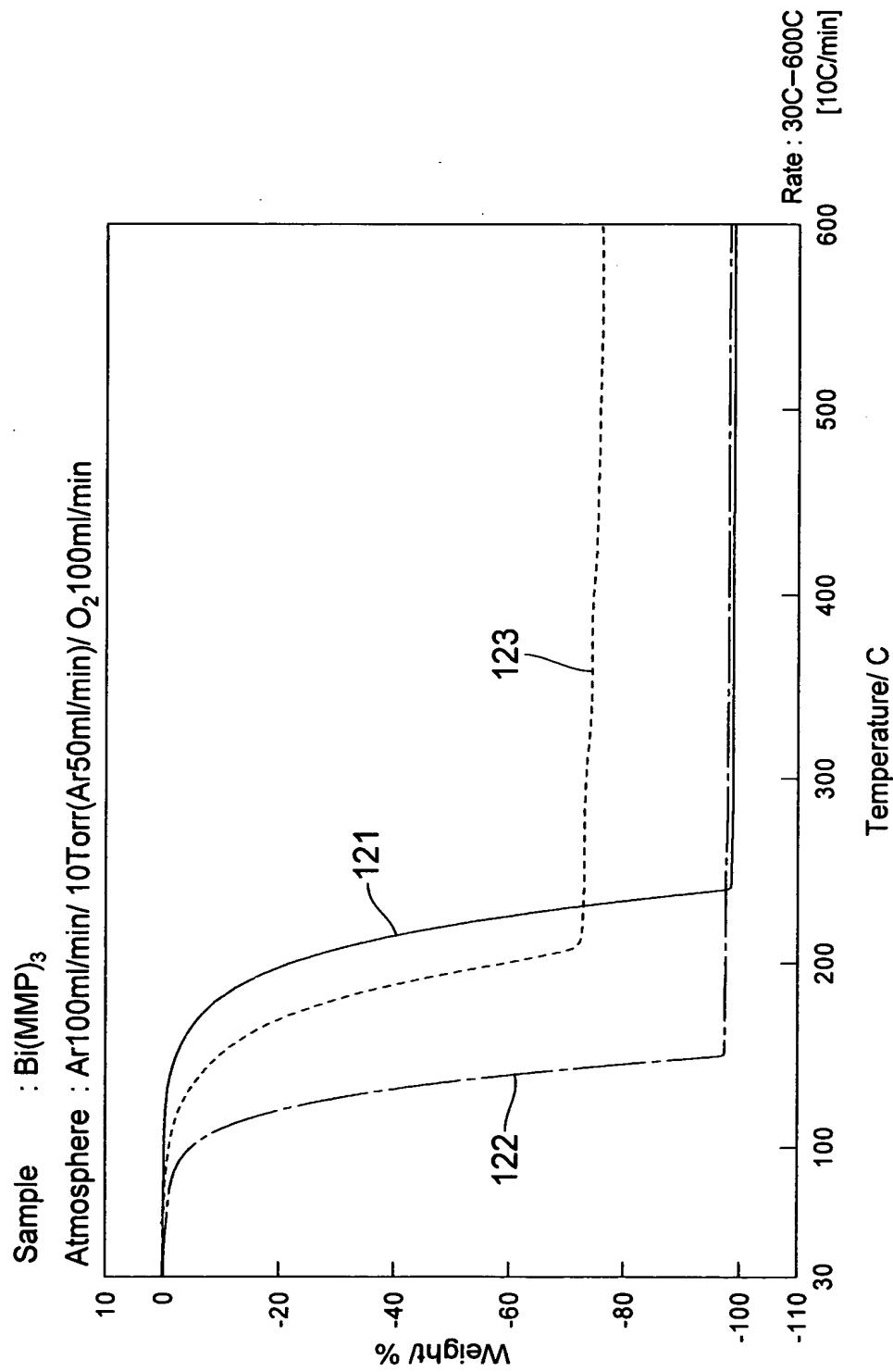


FIG. 13

10/526786

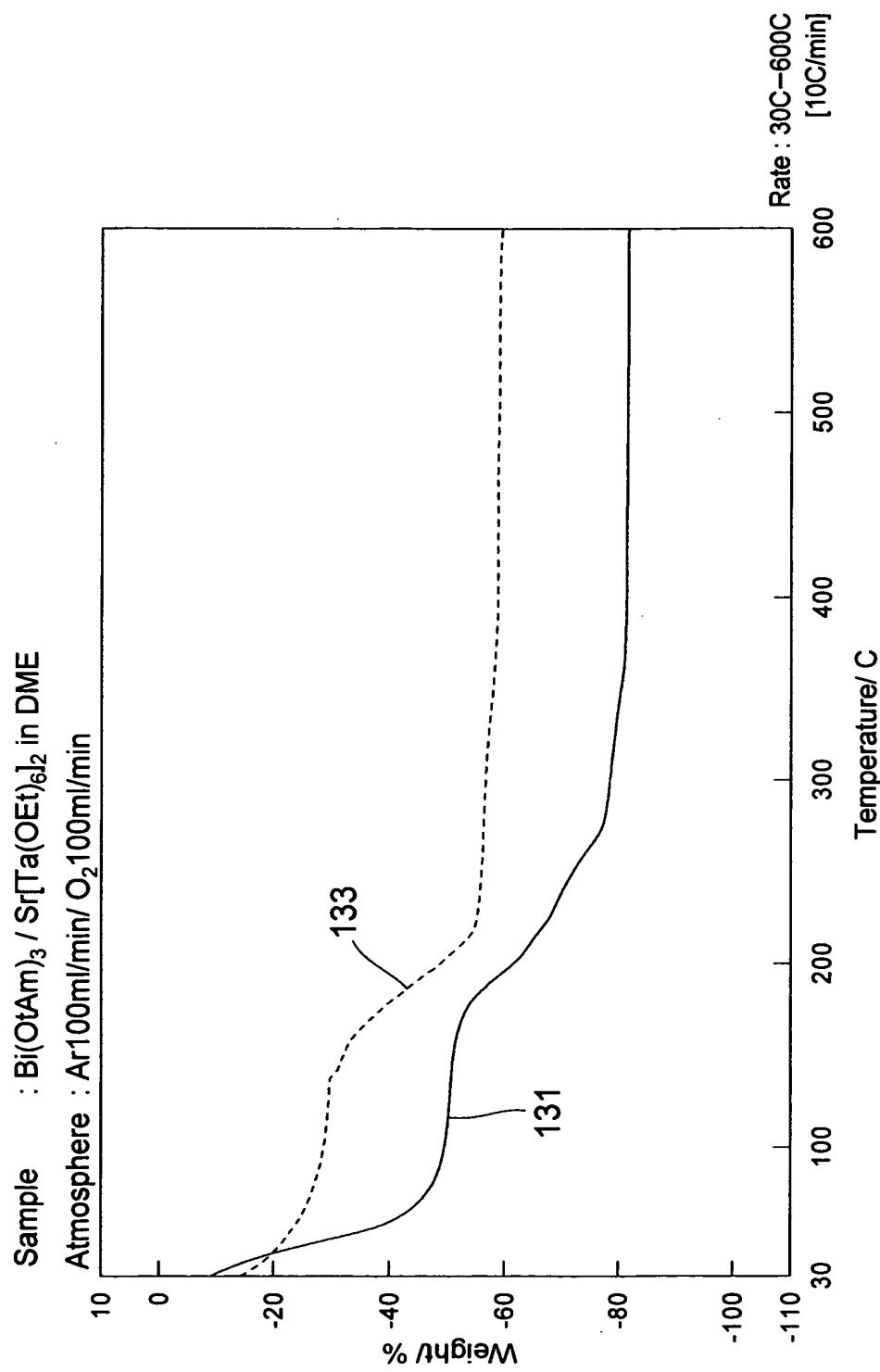


FIG.14

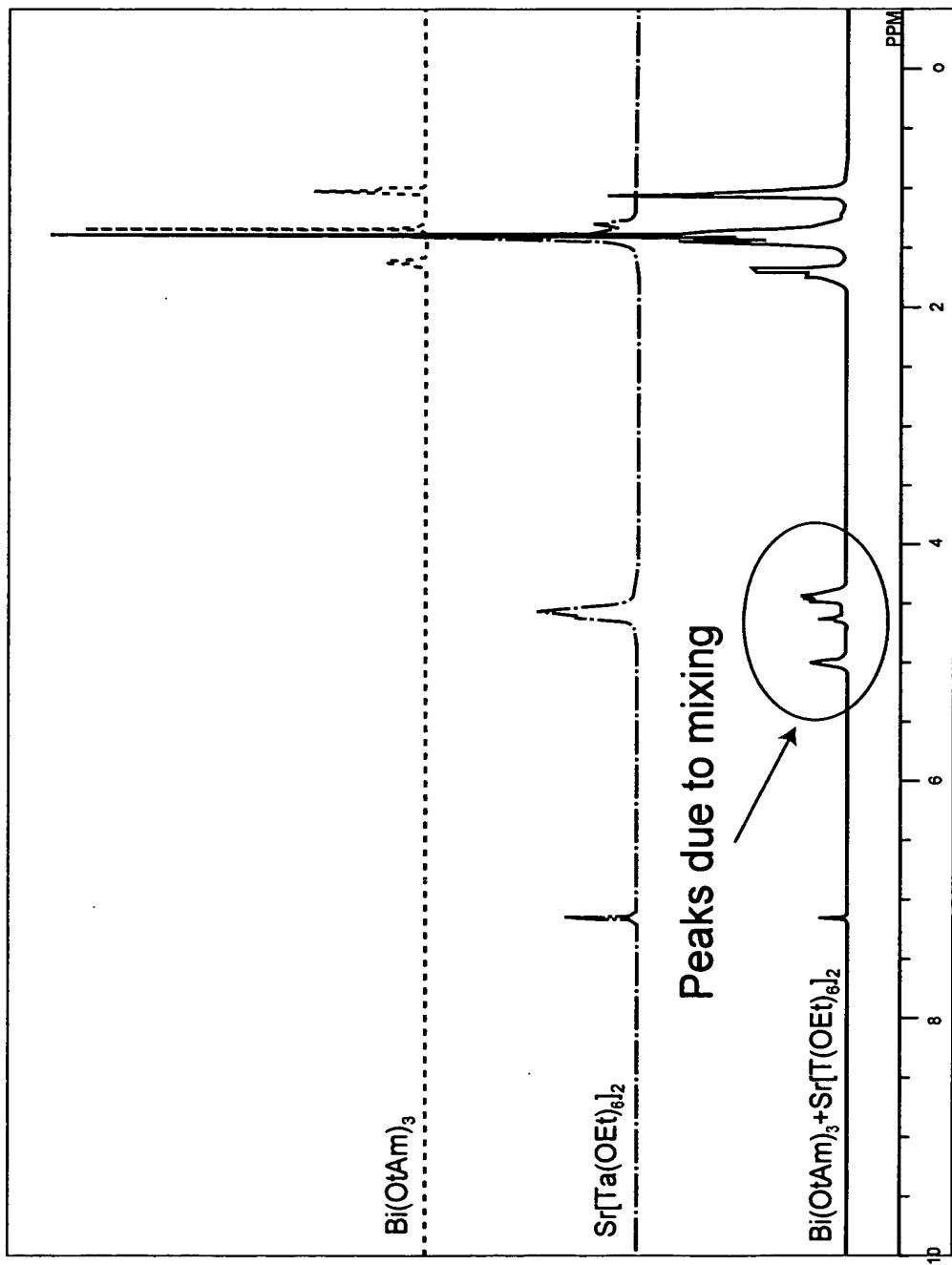


FIG.15

10/526786

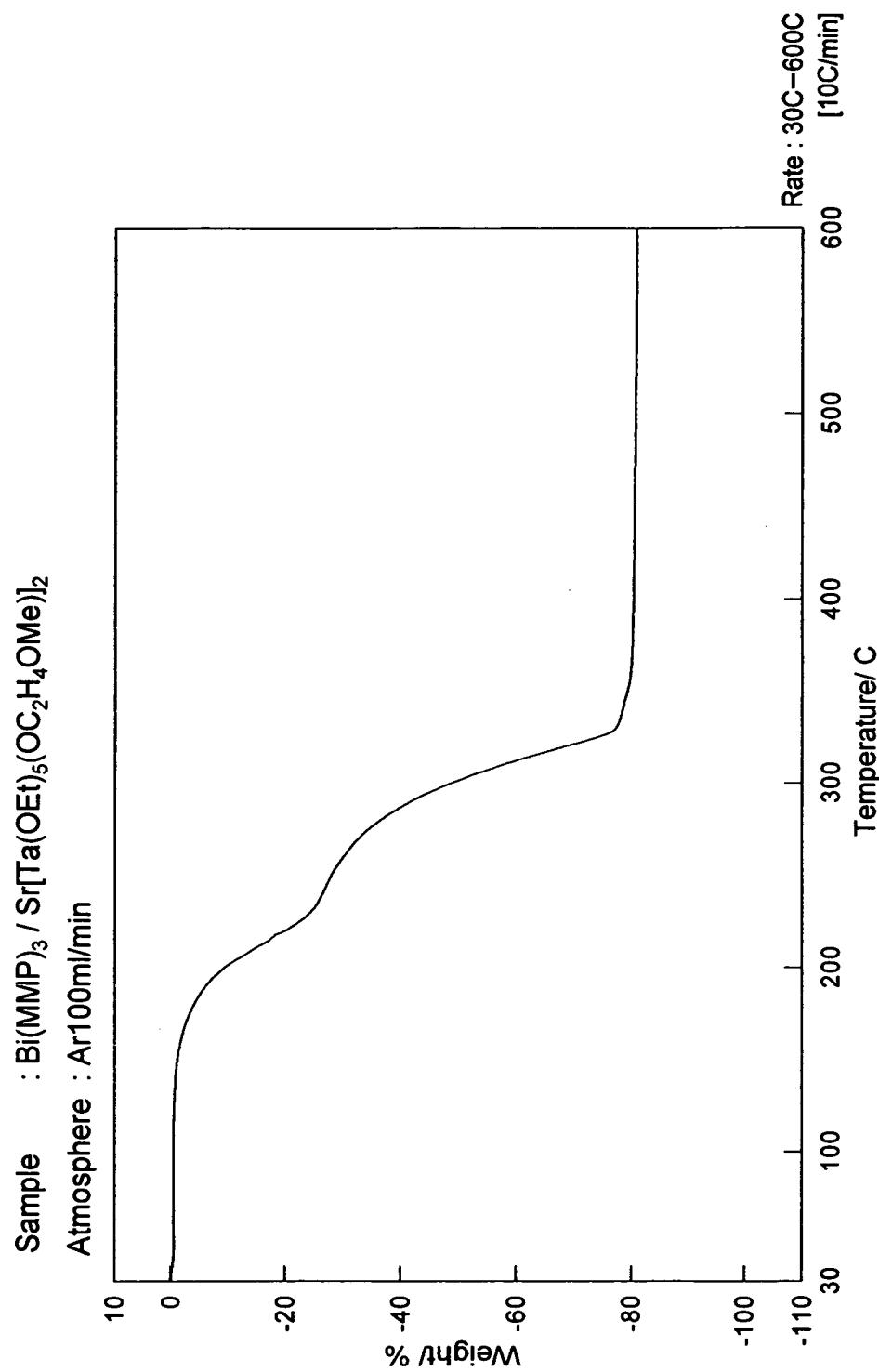


FIG.16

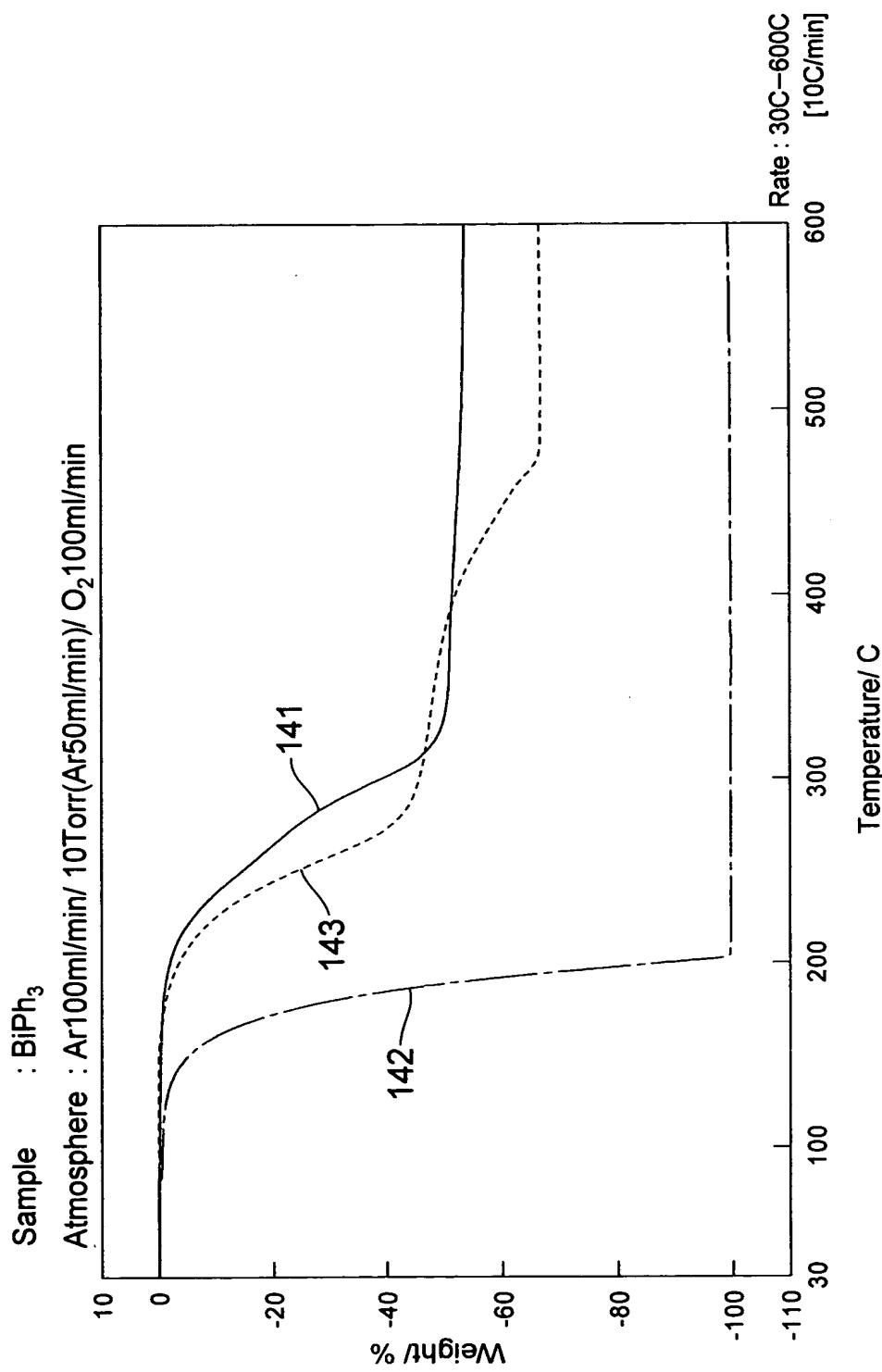


FIG. 17

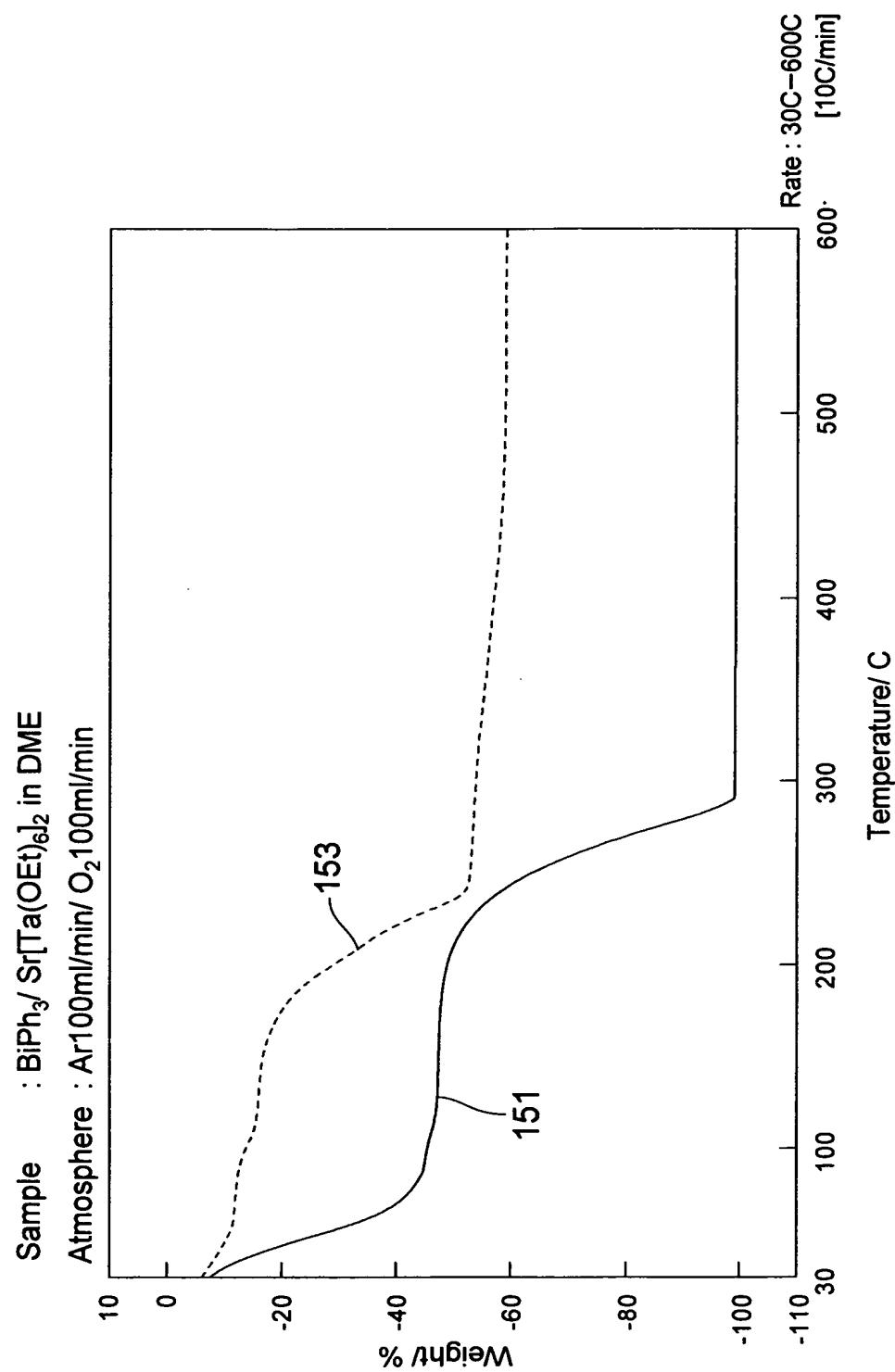


FIG. 18

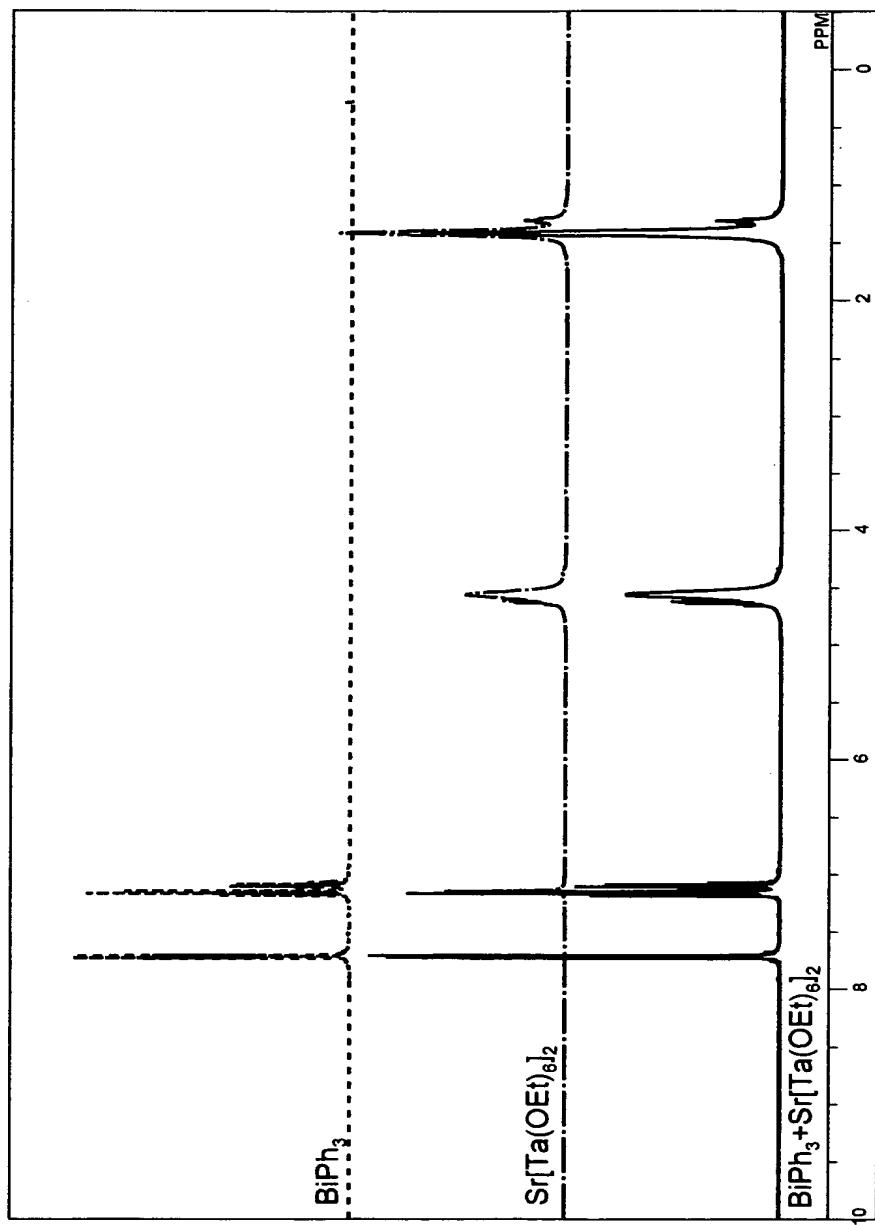


FIG.19

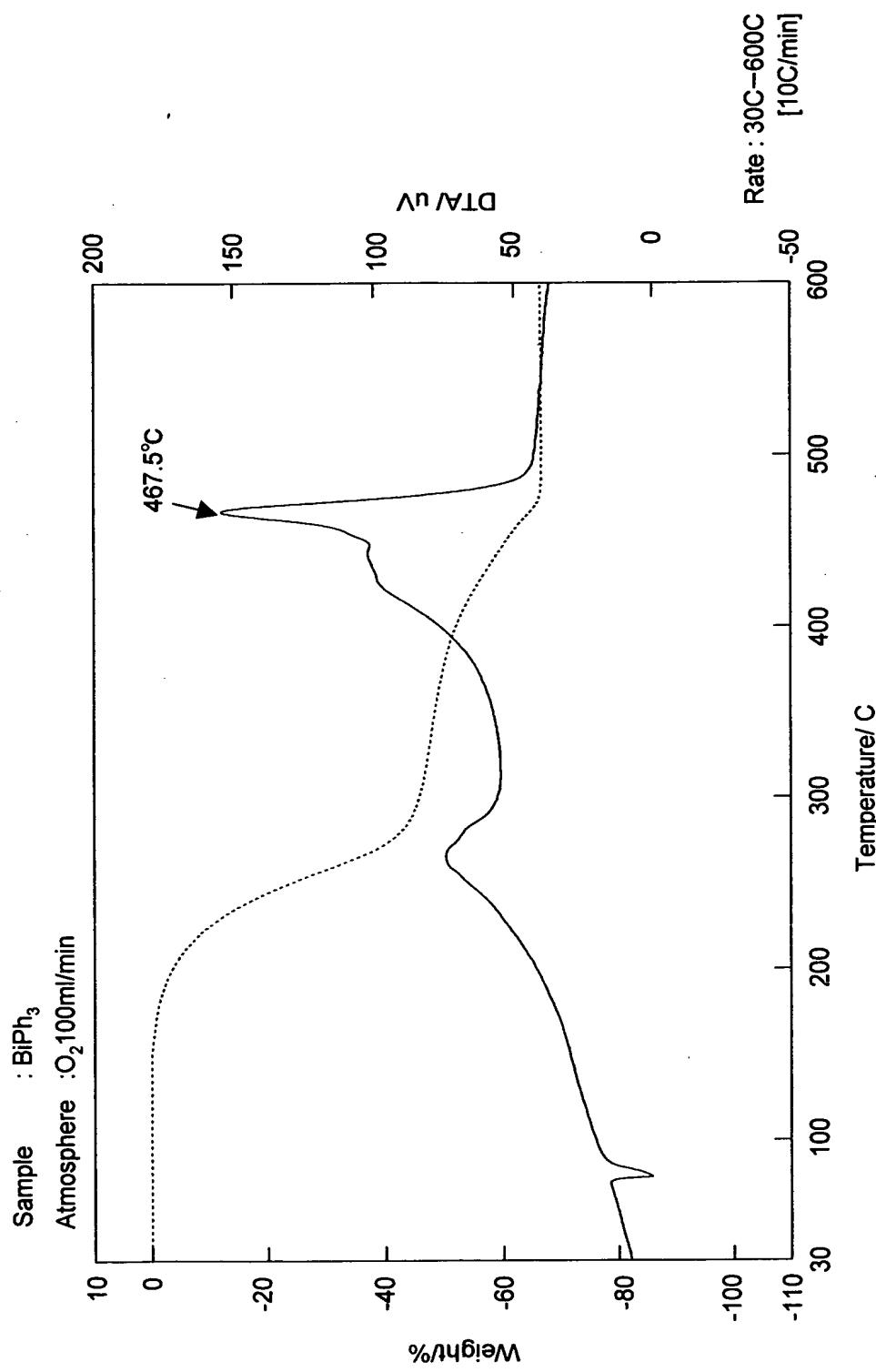


FIG.20